

## **SVC371**

°C

Diffused Junction Type Sillicon Diode

# Composite Varactor Diode for AM Receiver Low-Voltage Electronic Tuning Applications

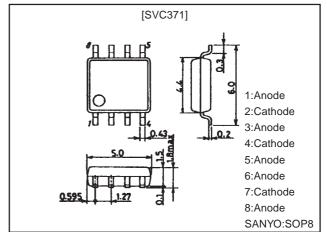
#### **Features**

- · Excellent large-input characteristics because of dualvaractor composite type.
- The number of manufacturing processes can be reduced and automatic mounting is possible because of composite type.
- · High capacitance ratio and high quality factor.
- Facilitates tuning circuit configuration because the cathodes of three dual-type elements are separated from each other, resulting in almost no interelement coupling.
- · Possible to offer the SVC371 devices in a tape reel packaging.
- · Surface mount type.

## **Package Dimensions**

unit:mm

1268



## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Reverse Voltage	٧ <sub>R</sub>		16	V
Junction Temperature	Tj		125	
Storage Temperature	Tstg		-55 to +125	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Oill
Breakdown Voltage	V <sub>(BR)R</sub>	I <sub>R</sub> =10μA	16			V
Reverse Current (One diode)	I <sub>R</sub>	V <sub>R</sub> =20V			100	nA
Interterminal Capacitance (Average)	C <sub>1V</sub>	V <sub>R</sub> =1V, f=1MHz*1	460*		540*	pF
	C <sub>6V</sub>	V <sub>R</sub> =6V, f=1MHz		50		pF
	C <sub>8V</sub>	V <sub>R</sub> =8V, f=1MHz	19		26	pF
Quality Factor	Q	V <sub>R</sub> =1V, f=1MHz	200			
Capacitance Ratio	CR	C <sub>1V</sub> /C <sub>8V</sub> , f=1MHz	18.5			
Matching Tolerance*2	ΔC <sub>m</sub>	CRFN-COSC-0.25pF   / COSC, V <sub>R</sub> =1V, f=1MHz			2.5	%
		V <sub>R</sub> =6V, f=1MHz			3.0	%
		V <sub>R</sub> =8V, f=1MHz			3.0	%

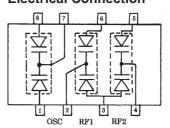
Note)\*1:1MHz signal:20mVrms.

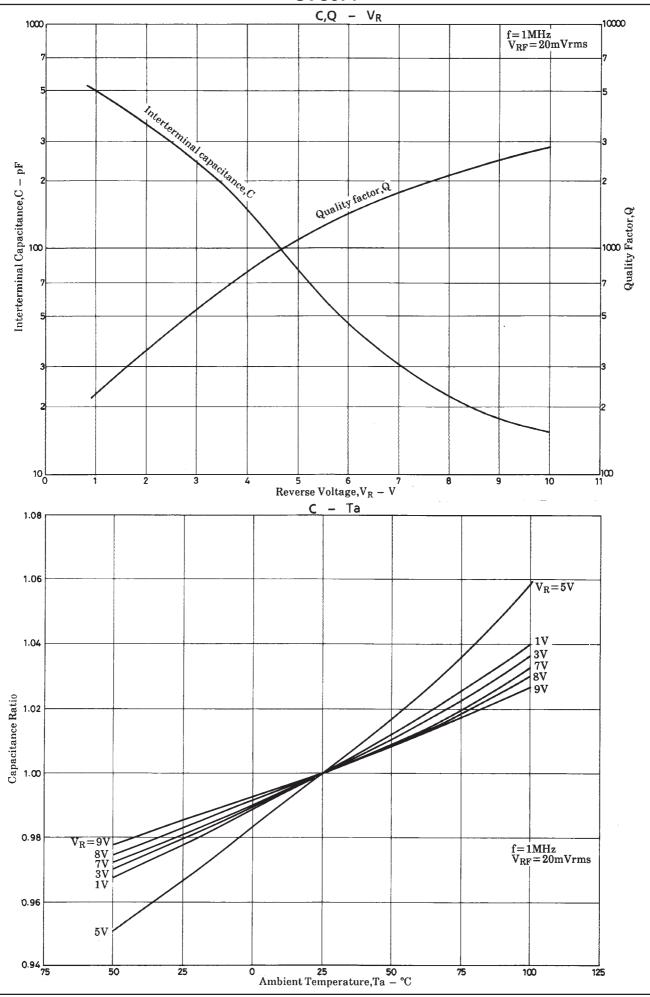
Note)\*2:Calculate using the average of tow diodes contained in each element of OSC, RF1, RF2.

Note)\*:The SVC371 is classified by  $C_{1V}$  as follows:

Rank	C <sub>1V</sub> (pF)
R	460.0 to 491.0
S	482.0 to 515.0
Т	505.0 to 540.0

## **Electrical Connection**





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